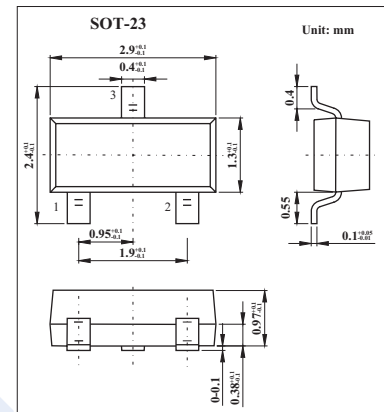
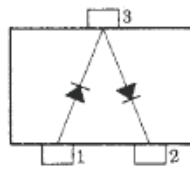


## Schottky Barrier Diode

### 1SS358

#### ■ Features

- Small interterminal capacitance
- Low forward voltage and excellent detection efficiency
- High breakdown voltage



#### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
peak reverse voltage	V <sub>R</sub>	55	V
Forward current	I <sub>F</sub>	10	mA
Power dissipation	P	150	mW
Junction Temperature	T <sub>j</sub>	125	°C
Storage Temperature range	T <sub>stg</sub>	-55 to + 125	°C

#### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 1 mA			0.35	V
Reverse voltage	V <sub>R</sub>	I <sub>R</sub> = 100 μ A	55			V
Forward Current	I <sub>F</sub>	V <sub>F</sub> = 1V	10			mA
Reverse current	I <sub>R</sub>	V <sub>R</sub> = 40V			50	μ A
Interterminal I capacitance	C	V <sub>R</sub> = 0, f = 1.0 MHz		0.45		pF

#### ■ Marking

Marking	DH